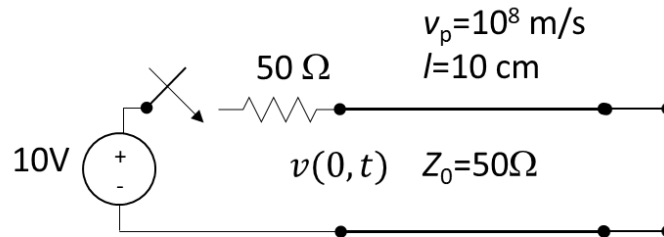


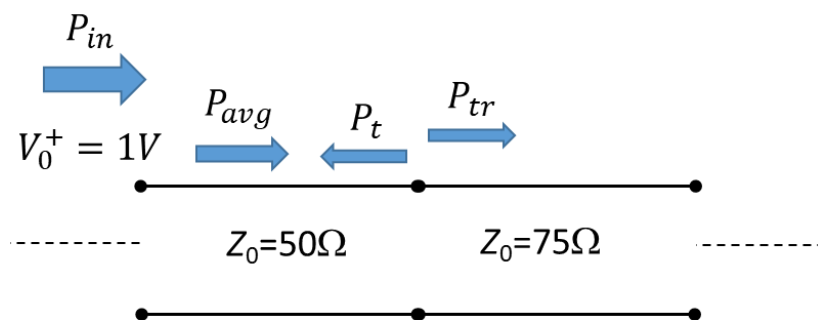
## High-speed electronics 2019 – Exercise 4

### “Transmission Lines and Gain”

- For a short-circuited transmission line connected to a constant voltage source (see below), we expect  $v(0, t) = 0$  after a long time. However, when we close the line, there should be a voltage wave travelling towards the short. Draw a bounce diagram and explain on how  $v(0, t)$  settles to 0V!



- A  $100\Omega$  transmission line has  $\epsilon_{eff}=1.5$  and is used at  $f=10$  GHz.
  - Find the *shortest* open-circuited stub making the line appear at a capacitance  $C_{in}=1$  pF.
  - Do the same for an inductance of  $L_{in}=1$  nH instead.
- A  $50\Omega$  source is injecting power ( $P_{in}$ ) with a voltage amplitude  $V_0^+ = 1V$  towards a  $50\Omega/75\Omega$  junction.
  - Calculate the injection and transmission coefficients.
  - Calculate the amplitude of  $V_0^-$  in the  $50\Omega$  region and  $V_0^+$  in the  $75\Omega$  region.
  - Calculate the input power  $P_{in}$ , the reflected power  $P_t$  and the transmitted power  $P_{tr}$ . Show that energy is conserved – i.e.  $P_{in} - P_t = P_{tr}$  and  $P_{avg} = P_{tr}$  despite a larger  $V_0^+$  in the  $75\Omega$  region.



- For the simplified NQS model, derive an expression for  $f_{max}$ , assuming that  $R_D=R_G=R_S=0$  (given  $C_{gs}, C_{gd}, g_m$  and  $g_d$ . Assume  $C_m=0$ )
- Parasitic capacitances add typically  $0.1-0.5$  fF/ $\mu m$  to  $C_{gs}$  and  $C_{gd}$ . For an InAs MOSFET with  $L_g=20$  nm,  $t_w=8$  nm,  $t_{ox}=5$  nm,  $\epsilon_{rox}=25$ ,
  - how large  $g_m$  is needed to obtain  $f_T > 1$  THz? (Assuming an optimistic  $R_D=R_S=0$  and  $g_d=0$ ).
  - Can this be reached with a (quasi-ballistic) FET?

6. A transistor is operated in saturation with  $g_m = 2000 \mu\text{S}/\mu\text{m}$ ,  $g_d = 10 \mu\text{S}/\mu\text{m}$ ,  $R_i = 30 \text{ Ohm}$ ,  $C_{gs} = 3\text{fF}/\mu\text{m}$ ,  $C_{gd} = 0.3 \text{ fF}/\mu\text{m}$ . We neglect parasitic capacitances. Calculate the following at 60 GHz: Consider the width of the transistor to be  $10\mu\text{m}$  for calculations.
- The Stern stability factor of the device.
  - What is the maximum stable gain?
  - What is the maximum available gain?
  - Is the device stable at 60 GHz? If not then unilaterize the device and calculate U.